

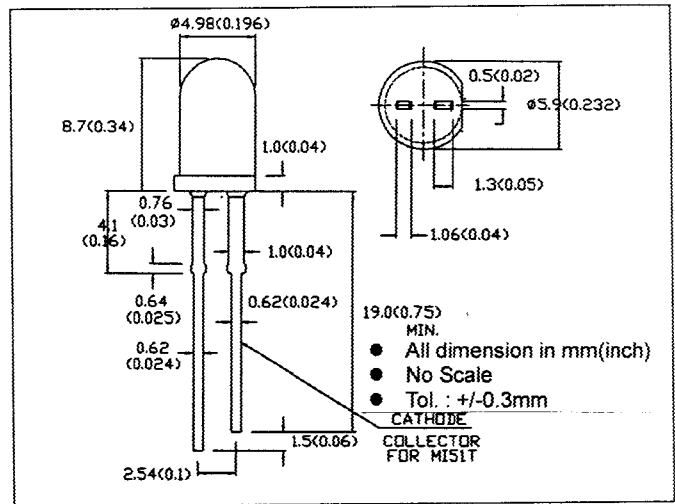
# MICRO ELECTRONICS

MI51T

INFRARED  
EMITTING  
DIODE

## DESCRIPTION

MI51T is GaAlAs infrared emitting diode molded in T-1 3/4 standard 5mm diameter clear transparent lens.



## ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	5V
Power Dissipation	75mW
Operating Temperature Range	-25 to +85°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

\* Pulse Width = 10μs, Duty Ratio = 0.01.

## ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	Po	1.0			mW	IF=20mA
Forward Voltage	VF		1.2	1.6	V	IF=20mA
Reverse Current	IR			100	μA	VR=5V
Half Intensity Beam Angle	θHI		50		degree	IF=20mA
Peak Wavelength	λp		940		nm	IF=20mA
Spectrum Line Half Width	Δλ		45		nm	IF=20mA



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